Journal of Crystal Growth 131 (1993) 621–625
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Abbona, F., F. Christensson, M. Franchini Angela and H.E. Lundager Madsen, Crystal habit and growth conditions of brushite, $CaHPO_4 \cdot 2H_2O$ 131 (1993) 331
Agarwal, M.K., see Arora 131 (1993) 268
Agranat, A., see Hofmeister 131 (1993) 486
Albers, C., see Zimmermann 131 (1993) 276
Anselmo, A., V. Prasad, J. Koziol and K.P. Gupta, Numerical and experimental study of a solid pellet feed continuous Czochralski growth process for silicon single crystals 131 (1993) 247
Arora, S.K., D.H. Patel and M.K. Agarwal, Vapour growth of SnS_2 single crystals 131 (1993) 268
Ashizawa, Y., see Naritsuka 131 (1993) 186

Baek, S.J., J.S. Chang, E.S. Choi and H.H. Lee, Axial dopant distribution and its control in bulk crystal growth 131 (1993) 481
Bähr, G., see Möller 131 (1993) 165
Balzuweit, K., A. Hovestad, H. Meekes and J.L. de Boer, The temperature and composition dependence of the modulation wave vector of incommensurate calaverite 131 (1993) 518
Bamberger, C.E., and O.C. Kopp, Acicular crystals of sodium tungsten bronzes 131 (1993) 473
Barrette, P., B. Michel and E. Stander, On the reproduction of ice from a common seed 131 (1993) 153
Baxter, C.S., W.M. Stobbs, R.F. Broom and J.P. Reithmaier, Observation of a novel form of ordering in $Al_{0.5}In_{0.5}As$ and $(Ga, Al)_{0.5}In_{0.5}As$ 131 (1993) 410
Bauser, E., see Weishart 131 (1993) 17
Becker, C.R., see Waag 131 (1993) 607
Benaissa, M., J. Werckmann, J.L. Hutchison, E. Peschiera, J. Guille and M.J. Ledoux, High-resolution transmission electron microscopy study on SiC grown from SiO and C*: crystal growth and structural characterization 131 (1993) 5
Benz, K.W., see Weishart 131 (1993) 17
Benz, K.W., see Zimmermann 131 (1993) 276
Benz, K.W., see Eckstein 131 (1993) 453
Berger, H., see Bickmann 131 (1993) 133
Bickmann, K., J. Hauck, P. Möck and H. Berger, Monoclinic deformation and tilting of epitaxial CdTe films on GaAs at 25–400°C 131 (1993) 133
Blanton, T.N., see Wernberg 131 (1993) 176
Bowman, L.E., see Cook 131 (1993) 395
Boyn, R., see Zimmermann 131 (1993) 276
Briones, F., see Mazuelas 131 (1993) 465
Brokman, A., see Vilenkin 131 (1993) 239
Broom, R.F., see Baxter 131 (1993) 419
Bucher, E., see Kloc 131 (1993) 448
Buhl, H. and R. Weiss, Carbon fibre spring for high-temperature application 131 (1993) 470
Byrne, E.K., see Karlicek, Jr. 131 (1993) 204

Carlin, J.F., A. Rudra and M. Ilegems, Quantitative study of the incorporation of group III elements in chemical beam epitaxy of GaInAsP alloys 131 (1993) 387
Červeň, I., T. Lacko, I. Novotný, V. Tvarožek and M. Harvanka, Texture of obliquely sputtered ZnO thin films 131 (1993) 546
Chang, J.S., see Baek 131 (1993) 481
Chatchaturov, A., see Polity 131 (1993) 271
Chichibu, S., S. Shirakata, A. Iwai, S. Matsumoto, H. Higuchi and S. Isomura, $CuAlSe_2$ chalcopyrite epitaxial layers grown by low-pressure metalorganic chemical vapor deposition 131 (1993) 551
Choi, E.S., see Baek 131 (1993) 481
Christensson, F., see Abbona 131 (1993) 331
Christov, M. and G.K. Kirov, The ratio of dissolving surface area/growing surface area in the hydrothermal growth of quartz 131 (1993) 560
Cihlář, A., see Nitsch 131 (1993) 612
Coblentz, D.L., see Karlicek, Jr. 131 (1993) 204
Cook, A.P., L.E. Bowman and A.P. Wade, Study of $KBr/Pb(NO_3)_2$ growth and crystal morphologies by acoustic emission and photomicrographic techniques 131 (1993) 395

Danilewsky, A.N., see Weishart 131 (1993) 17
De Boer, J.L., see Balzuweit 131 (1993) 518
Desatnik, N., B. Subramaniam and B.E. Thompson, A nonisothermal film model for mass-transfer-limited selective epitaxial growth of silicon on patterned surfaces 131 (1993) 589
Duffar, T., see Harter 131 (1993) 157
Dusserre, P., see Harter 131 (1993) 157

Eckstein, J., B. Erler, C. Eiche and K.W. Benz, Growth of bulk lead di-iodide crystals from the vapour phase 131 (1993) 453
Eiche, C., see Zimmermann 131 (1993) 276
Eiche, C., see Eckstein 131 (1993) 453
Elliman, R.G., see Russo 131 (1993) 124
Erler, B., see Eckstein 131 (1993) 453
Eustathopoulos, N., see Harter 131 (1993) 157

Fawcett, P.N., see Zhang 131 (1993) 300
Filo, A.J., see Wernberg 131 (1993) 176
Franchini Angela, M., see Abbona 131 (1993) 331
Fripp, Jr., A.L., see Hubert 131 (1993) 75
Fujita, S., see Naritsuka 131 (1993) 186
Fukuda, T., see Hirata 131 (1993) 145
Fukuda, T., see Okano 131 (1993) 616
Furuse, H., see Yano 131 (1993) 620

Garandet, J.P., Microsegregation in crystal growth from the melt: an analytical approach 131 (1993) 431
González, L., see Mazuelas 131 (1993) 465
Griesche, J., see Reichow 131 (1993) 277
Guille, J., see Benaissa 131 (1993) 5
Gupta, K.P., see Anselmo 131 (1993) 247
Gupta, S.R., see Sharma 131 (1993) 565
Gysling, H.J., see Wernberg 131 (1993) 176

Haile, S.M., B.J. Wuensch, T. Siegrist and R.A. Laudise, Hydrothermal synthesis of new alkali silicates. I. Potassium neodymium phases 131 (1993) 352
Haile, S.M., B.J. Wuensch and R.A. Laudise, Hydrothermal synthesis of new alkali silicates. II. Sodium neodymium and sodium yttrium phases 131 (1993) 373
Han, T.P.J., see Sharp 131 (1993) 457
Hart, L., see Zhang 131 (1993) 300
Harter, I., P. Dusserre, T. Duffar, J.-Ph. Nabot and N. Eustathopoulos, Wetting of III–V melts on crucible materials 131 (1993) 157
Harvanka, M., see Červeň 131 (1993) 546
Hauck, see Bickmann 131 (1993) 133
Hayes, T.R., see Karlicek, Jr. 131 (1993) 204
Heinke, H., see Waag 131 (1993) 607
Henderson, B., see Sharp 131 (1993) 457
Henneberger, F., see Reichow 131 (1993) 277
Higuchi, H., see Chichibu 131 (1993) 551
Hildmann, B.O., see Möller 131 (1993) 165
Hirata, A., M. Tachibana, T. Sugimoto, Y. Okano and T. Fukuda, Control of crystal–melt interface shape during growth of lithium niobate single crystal 131 (1993) 145
Hoffmann, D.M., see Zimmermann 131 (1993) 276
Hoffmann, N., see Reichow 131 (1993) 277
Hofmeister, A. Yariv and A. Agranat, Growth and characterization of the perovskite $K_{1-y}Li_yTa_{1-x}Nb_xO_3$:Cu 131 (1993) 486
Honjo, H. and S. Ohta, Regular tip-splitting growth of an NH_4Cl dendrite 131 (1993) 111
Hoshikawa, K., see Okano 131 (1993) 616
Hosoi, N., see Ohshita 131 (1993) 495
Hovestad, A., see Balzuweit 131 (1993) 518
Hubert, J.A., A.L. Fripp, Jr. and C.S. Welch, Resolution of the discrepancy between temperature indicated interface and radiographically determined interface in a vertical Bridgman furnace 131 (1993) 75
Hutchison, J.L., see Benaissa 131 (1993) 5

Ikeya, T., see Okano 131 (1993) 616
Ilegems, M., see Carlin 131 (1993) 387
Illingworth, R., see Sharp 131 (1993) 457
Ingle, N.K., see Mountziaris 131 (1993) 283
Inoue, M., see Yano 131 (1993) 620
Inoue, T., T. Ohsuna, Y. Obara, Y. Yamamoto, M. Satoh and Y. Sakurai, Stripe-shaped facetted morphology and domain structure of epitaxial CeO_2(110) layers on Si(100) substrates 131 (1993) 347
Ishida, K., see Taki 131 (1993) 13
Ishikawa, H., see Mashita 131 (1993) 61
Isomura, S., see Chichibu 131 (1993) 551
Iwai, A., see Chichibu 131 (1993) 551
Iwai, Y., see Yano 131 (1993) 620
Iwanaga, H., see Mochizuki 131 (1993) 41

Jacobs, K., see Reichow 131 (1993) 277
Janimak, J.J., see Point 131 (1993) 501
Jayavel, R., C. Sekar, P. Murugakoothan, C.R. Venkateswara Rao, C. Subramanian and P. Ramasamy, Growth of large size single crystals and whiskers of $Bi_2Sr_2CaCu_2O_8$ by step-cooling method 131 (1993) 105
Johnston, P.N., see Russo 131 (1993) 124
Joyce, B.A., see Zhang 131 (1993) 300

Kalyanasundaram, S., see Mountziaris 131 (1993) 283
Karlicek, Jr., R.F., D.L. Coblentz, R.A. Logan, T.R. Hayes, R. Pawelek and E.K. Byrne, A modified metalorganic chemical vapor deposition chemistry for improved selective area regrowth 131 (1993) 204
Kawakyu, Y., see Mashita 131 (1993) 61
Kirov, G.K., see Christov 131 (1993) 560
Kizuka, T., T. Sakamoto and N. Tanaka, Growth of fine crystals with A-15 type structure in vacuum-deposited tungsten films studied by high-resolution electron microscopy 131 (1993) 439
Kloc, Ch., G. Willeke and E. Bucher, Flux growth and electrical transport measurements of pyrite (FeS_2) 131 (1993) 448
Kobayashi, J., Y. Tazoh and S. Miyazawa, Epitaxial growth of $NdGaO_3$ thin films on (100) $SrTiO_3$ substrates 131 (1993) 138

Kopp, O.C., see Bamberger 131 (1993) 473
Koziol, J., see Anselmo 131 (1993) 247
Krause-Rehberg, R., see Polity 131 (1993) 271

Lacko, T., see Červeň 131 (1993) 546
Landwehr, G., see Waag 131 (1993) 607
Lanig, P., see Stein 131 (1993) 71
Laudise, R.A., see Haile 131 (1993) 352
Laudise, R.A., see Haile 131 (1993) 373
Laurila, J., see Tappura 131 (1993) 309
Lawrence, D.J., see Wernberg 131 (1993) 176
Ledoux, M.J., see Benaissa 131 (1993) 5
Lee, H.H., see Baek 131 (1993) 481
Li, H.M., see Yoon 131 (1993) 1
Li, J., J. Sun and Z. Saghir, Buoyant and thermocapillary flow in liquid encapsulated floating zone 131 (1993) 83
Logan, R.A., see Karlicek, Jr. 131 (1993) 204
Loiacono, D.N., see Loiacono 131 (1993) 323
Loiacono, G.M., D.N. Loiacono and R.A. Stolzenberger, Crystal growth and characterization of ferroelectric $CsTiOAsO_4$ 131 (1993) 323
Louchev, O.A., Onset of supercooling in front of the solidification interface in zone melting materials processing 131 (1993) 209
Lu Taijing, see Ng 131 (1993) 265
Lundager Madsen, H.E., see Abbona 131 (1993) 331

Mäkinen, S., see Polity 131 (1993) 271
Málková, Z., see Nitsch 131 (1993) 612
Mann, S., see Titiloye 131 (1993) 533
Maruyama, H., K. Pak, K. Sakakibara, H. Yonezu and Y. Takano, Study on initial growth process of Si on InP(100) substrate grown by molecular beam epitaxy 131 (1993) 316
Mashita, M., M. Sasaki, Y. Kawakyu and H. Ishikawa, Surface reaction mechanisms in GaAs atomic layer epitaxy 131 (1993) 61
Masumoto, K., see Mochizuki 131 (1993) 41
Matsumoto, S., see Chichibu 131 (1993) 551
Matsushige, K., see Taki 131 (1993) 13
Mazuelas, A., L. González, F.A. Ponce, L. Tapfer and F. Briones, Critical thickness determination of InAs, InP and GaP on GaAs by X-ray interference effect and transmission electron microscopy 131 (1993) 465
Meekes, H., see Balzuweit 131 (1993) 518
Meyer, B.K., see Zimmermann 131 (1993) 276
Michel, B., see Barrette 131 (1993) 153
Miyazawa, S., see Kobayashi 131 (1993) 138
Miyazawa, S., see Sasaura 131 (1993) 413
Mochizuki, K., E. Niwa, H. Iwanaga and K. Masumoto, Some characteristics of $AgGaS_2$ single crystals grown from the melt 131 (1993) 41
Möck, P., see Bickmann 131 (1993) 133
Möller, U., B.O. Hildmann and G. Bähr, Shape of the solid–liquid interface and dopant distribution of Bridgman grown Ge:Ga 131 (1993) 165
Mountziaris, T.J., S. Kalyanasundaram and N.K. Ingle, A reaction-transport model of GaAs growth by metalorganic chemical vapor deposition using trimethyl-gallium and tertiary-butyl-arsine 131 (1993) 283
Muggelberg, C., see Reichow 131 (1993) 277
Murugakoothan, P., see Jayavel 131 (1993) 105

Nabot, J.-Ph., see Harter 131 (1993) 157
Naritsuka, S., T. Noda, A. Wagai, S. Fujita and Y. Ashizawa, Electrical properties and deep levels of InAlAs layers grown by metalorganic chemical vapor deposition 131 (1993) 186
Nayyar, N.K., see Sharma 131 (1993) 565
Neave, J.H., see Zhang 131 (1993) 300
Ng, S.C. and Lu Taijing, Detection of oxidation stacking faults in silicon wafers by a multipass Fabry–Perot Rayleigh–Brillouin scattering spectrometer 131 (1993) 265
Nikolov, V., see Varadinov 131 (1993) 97
Nitsch, K., A. Cihlář, Z. Málková, M. Rodová and M. Vaněček, The purification and preparation of high-purity $PbCl_2$ and ternary alkali lead chloride single crystals 131 (1993) 612
Niwa, E., see Mochizuki 131 (1993) 41
Noda, T., see Naritsuka 131 (1993) 186
Novotný, I., see Červeň 131 (1993) 546

Obara, Y., see Inoue 131 (1993) 347
Ohshita, Y. and N. Hosoi, In-situ monitoring of surface reactions in Si vapor phase epitaxial growth by surface photo-absorption method 131 (1993) 495
Ohsuna, T., see Inoue 131 (1993) 347
Ohta, S., see Honjo 131 (1993) 111
Okabe, H., see Taki 131 (1993) 13
Okano, Y., see Hirata 131 (1993) 145
Okano, Y., T. Ikeya, K. Hoshikawa and T. Fukuda, Behavior of $RAlO_3$ (R = Ho, Er and Dy) during crystal growth by the Czochralski method 131 (1993) 616
Osadchuk, V.V., see Oseledchik 131 (1993) 199
Oseledchik, Yu.S., V.V. Osadchuk, A.L. Prosvirnin and A.F. Selevich, Growth of high-quality barium metaborate crystals from Na_2O–NaF solution 131 (1993) 199

Pain, G.N., see Russo 131 (1993) 124
Pak, K., see Maruyama 131 (1993) 316
Palosz, W. and H. Wiedemeier, Residual gas pressures in sealed fused silica glass ampoules 131 (1993) 193
Parker, S.C., see Titiloye 131 (1993) 533

Pashley, D.W., see Zhang 131 (1993) 300
Patel, D.H., see Arora 131 (1993) 268
Pawelek, R., see Karlicek, Jr. 131 (1993) 204
Peschiera, E., see Benaissa 131 (1993) 5
Peshev, P., see Varadinov 131 (1993) 97
Pet'kov, I.S. and B.S. Red'kin, Calculation of the stationary cross-section form of non-axisymmetrical crystals growing from the melt 131 (1993) 598
Point, J.-J. and J.J. Janimak, An evaluation of the theories of regimes of nucleation controlled crystal growth as applied to polymers 131 (1993) 501
Polity, A., R. Krause-Rehberg, V. Zlomanov, V. Stanov, A. Chatchaturov and S. Mäkinen, Study of vacancy defects in PbSe and $Pb_{1-x}Sn_xSe$ by positron annihilation 131 (1993) 271
Ponce, F.A., see Mazuelas 131 (1993) 465
Prasad, V., see Anselmo 131 (1993) 247
Prosvirnin, A.L., see Oseledchik 131 (1993) 199

Radhakrishan, K. see Yoon 131 (1993) 1
Ramasamy, P., see Jayavel 131 (1993) 105
Red'kin, B.S., see Pet'kov 131 (1993) 598
Reichow, J., J. Griesche, N. Hoffmann, C. Muggelberg, H. Rossmann, L. Wilde, F. Henneberger and K. Jacobs, Molecular beam epitaxial growth and characterization of ZnSe of GaAs 131 (1993) 277
Reithmaier, J.P., see Baxter 131 (1993) 419
Rodová, M., see Nitsch 131 (1993) 612
Rodriguez, R., see Torrent 131 (1993) 115
Rossmann, H., see Reichow 131 (1993) 277
Ruddock, I.S., see Sharp 131 (1993) 457
Rudolph, P., see Zimmermann 131 (1993) 276
Rudra, A., see Carlin 131 (1993) 387
Rueter, M.A. and J.M. Vohs, The chemistry of the initial stages of the growth of ZnSe on GaAs(100) using diethylzinc and diethylselenium precursors 131 (1993) 49
Russo, S.P., G.N. Pain, P.N. Johnston and R.G. Elliman, Determination of composition, thickness and growth rate profiles of MOCVD grown $Hg_{1-x}Cd_xTe$ 131 (1993) 124

Saghir, Z., see Li 131 (1993) 83
Sakakibara, K., see Maruyama 131 (1993) 316
Sakamoto, T., see Kizuka 131 (1993) 439
Sakurai, Y., see Inoue 131 (1993) 347
Sasaki, M., see Mashita 131 (1993) 61
Sasaura, M. and S. Miyazawa, Twin-free single crystal growth of $NdGaO_3$ 131 (1993) 413
Satoh, M., see Inoue 131 (1993) 347
Scholl, S., see Waag 131 (1993) 607
Sekar, C., see Jayavel 131 (1993) 105
Selevich, A.F., see Oseledchik 131 (1993) 199
Sha, Y.-G., C.-H. Su and F.R. Szofran, Thermodynamic analysis and mass flux of the $HgZnTe–HgI_2$ chemical vapor transport system 131 (1993) 574
Sharma, B.B., see Sharma 131 (1993) 565
Sharma, R.K., V.K. Singh, N.K. Nayyar, S.R. Gupta and B.B. Sharma, Horizontal casting for the growth of $Hg_{1-x}Cd_xTe$ by solid state recrystallization 131 (1993) 565
Sharp, J.H., T.P.J. Han, B. Henderson, R. Illingworth and I.S. Ruddock, Dopant incorporation in single-crystal fibre growth by the laser-heated miniature pedestal growth technique 131 (1993) 457
Shirakata, S., see Chichibu 131 (1993) 551
Sidawi, I.M.S. and S.N. Tewari, Macrosegregation during plane front directional solidification of CsI–1 wt% TlI alloy 131 (1993) 230
Siegrist, T., see Haile 131 (1993) 352
Sinerius, D., see Zimmermann 131 (1993) 276
Singh, V.K., see Sharma 131 (1993) 565
Sluyters, J.H., see Torrent 131 (1993) 115
Stander, E., see Barrette 131 (1993) 153
Stanov, V., see Polity 131 (1993) 271
Stein, R.A. and P. Lanig, Control of polytype formation by surface energy effects during the growth of SiC monocrystals by the sublimation method 131 (1993) 71
Stobbs, W.M., see Baxter 131 (1993) 419
Stoica, T. and L. Vescan, Misfit dislocations in finite lateral size $Si_{1-x}Ge_x$ films grown by selective epitaxy 131 (1993) 32
Stolzenberger, R.A., see Loiacono 131 (1993) 323
Su, C.-H., see Sha 131 (1993) 574
Subramanian, B., see Desatnik 131 (1993) 589
Subramanian, C., see Jayavel 131 (1993) 105
Sugimoto, T., see Hirata 131 (1993) 145
Sun, J., see Li 131 (1993) 83
Szofran, F.R., see Sha 131 (1993) 574

Tachibana, M., see Hirata 131 (1993) 145
Taguchi, F., see Watanabe 131 (1993) 181
Takano, Y., see Maruyama 131 (1993) 316
Taki, S., K. Ishida, H. Okabe and K. Matsushige, Direct observation of the growth process of organic crystals by scanning tunnelling microscopy 131 (1993) 13
Tanaka, N., see Kizuka 131 (1993) 439
Tapfer, L., see Mazuelas 131 (1993) 465
Tappura, K. and J. Laurila, Unstable regions in the growth of GaInAsP by gas-source molecular beam epitaxy 131 (1993) 309
Tazoh, Y., see Kobayashi 131 (1993) 138
Tewari, S.N., see Sidawi 131 (1993) 230
Thompson, B.E., see Desatnik 131 (1993) 589
Titiloye, J.O., S.C. Parker and S. Mann, Atomistic simulation of calcite surfaces

and the influence of growth additives on their morphology 131 (1993) 533
Torrent, J., R. Rodriguez and J.H. Sluyters, The induction time in the electrocrystallization of lead chloride and lead sulphate on an amalgamated lead electrode 131 (1993) 115
Tvarožek, V., see Červeň 131 (1993) 546

Vanecek, M., see Nitsch 131 (1993) 612
Varadinov, R., V. Nikolov and P. Peshev, Growth of single crystals of Ga-, Al- or (Mn + Ti)-substituted barium hexaferrite 131 (1993) 97
Venkateswara Rao, C.R., see Jayavel 131 (1993) 105
Vescan, L., see Stoica 131 (1993) 32
Vilenkin, A.J. and A. Brokman, Geometric model of crystal growth between rigid walls. III. Kinetic faceting in presence of preferred interface inclination 131 (1993) 239
Vohs, J.M., see Rueter 131 (1993) 49

Waag, A., H. Heinke, S. Scholl, C.R. Becker and G. Landwehr, Growth of MgTe and $Cd_{1-x}Mg_xTe$ thin films by molecular beam epitaxy 131 (1993) 607
Wade, A.P., see Cook 131 (1993) 395
Wagai, A., see Naritsuka 131 (1993) 186
Watanabe, K. and F. Taguchi, Growth of fine and mono-sized Cr:YAG single crystals from KF solvent 131 (1993) 181
Weishart, H., A.N. Danilewsky, K.W. Benz and E. Bauser, Morphological stability during GaAs solution growth: liquid phase epitaxy versus the travelling heater method 131 (1993) 17
Weiss, R., see Buhl 131 (1993) 470
Welch, C.S., see Hubert 131 (1993) 75
Werckmann, J. see Benaissa 131 (1993) 5
Wernberg, A.A., D.J. Lawrence, H.J. Gysling, A.J. Filo and T.N. Blanton, Epitaxial growth of gallium arsenide thin films by spray pyrolysis using a single-source organometallic precursor 131 (1993) 176
Wiedemeier, H., see Palosz 131 (1993) 193
Wilde, L., see Reichow 131 (1993) 277
Willeke, G., see Kloc 131 (1993) 448
Wuensch, B.J., see Haile 131 (1993) 352
Wuensch, B.J., see Haile 131 (1993) 373

Yamamoto, Y., see Inoue 131 (1993) 347
Yano, M., H. Furuse, Y. Iwai, K. Yoh and M. Inoue, Raman scattering analysis of InAs/GaSb ultrathin-layer superlattices grown by molecular beam epitaxy (E) 131 (1993) 620
Yariv, A., see Hofmeister 131 (1993) 486
Yoh, K., see Yano 131 (1993) 620
Yonezu, H., see Maruyama 131 (1993) 316
Yoon, S.F., H.M. Li, K. Radhakrishnan and D.H. Zhang, The effect of growth interruption on the photoluminescence linewidth of GaAs/InGaAs quantum wells grown by molecular beam epitaxy 131 (1993) 1

Zhang, D.H., see Yoon 131 (1993) 1
Zhang, X., D.W. Pashley, L. Hart, J.H. Neave, P.N. Fawcett and B.A. Joyce, The morphology and asymmetric strain relief behaviour of InAs films on GaAs(110) grown by molecular beam epitaxy 131 (1993) 300
Zimmermann, H., R. Boyn, P. Rudolph, C. Albers, K.W. Benz, D. Sinerius, C. Eiche, B.K. Meyer and D.M. Hoffmann, State and distribution of point defects in doped and undoped Bridgman-grown CdTe single crystals (E) 131 (1992) 276
Zlomanov, V., see Polity 131 (1993) 271
Zytkiewicz, Z.R., Influence of convection on the composition profiles of thick GaAlAs layers grown by liquid phase electroepitaxy 131 (1993) 426

Journal of Crystal Growth 131 (1993) 626–628
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index

Alkali
– lead chlorides, ternary 612
Alumina 457
Aluminum
– gallium arsenide 61, 426
– gallium indium arsenide 419
– indium arsenide 419
Ammonium
– chloride 111
Apparatus
– for melt growth
– – by Czochralski method
– – – of silicon 247
– for miscellaneous purposes
– – acoustic emission analysis during crystal growth 395
– – high temperature carbon fiber spring 470
– – wetting measurement 157

Barium
– hexaferrite 97
– metaborate 199
Bismuth
– strontium calcium cuprate 105

Cadmium
– magnesium telluride 607
– telluride 133
Calcite 533
Calcium
– hydrogen orthophosphate dihydrate 331
Carbon
– fiber spring 470
Cerium
– dioxide 347
Cesium
– iodide 230
– titanyl arsenate 323
Clusters
– of interface in Bridgman furnace 75
Computer simulation
– of calcite morphology 533
– of metalorganic chemical vapor deposition 283
– of temperature field 247
– of temperature and velocity fields in floating zone 83
Constitutional supercooling
– theory of 209
Convection 145, 165, 247, 431
Copper
– aluminum selenide 551

Dendritic growth
– of ammonium chloride 111
– of lead di-iodide 453
Device characterization
– quantum wells 1, 620
– scintillators 230
Diffusional control
– of dopant transport 165
Dissolution
– of sodium tungsten bronzes 473

Epitaxy, see Thin film growth
Etching
– chemical 32, 413, 565

Gadolinium
– molybdate 598
Gallium
– antimonide 157, 620
– arsenide 1, 17, 61, 83, 176, 283
– germanium 75, 165
– indium arsenide 1, 387
– indium arsenide phosphide 309, 387
– indium phosphide 387
– phosphide 465
– scandium aluminum garnet 457
Garnets 181, 457
Germanium 75
Gold
– silver telluride 518

Hydrodynamics, see Convection

Ice 153
Indium
– aluminum arsenide 186, 300, 465
– antimonide 157
– arsenide 300, 465, 620
– phosphide 204, 465
Iron
– sulphide 448

Kinetics
– of growth 13, 17, 49, 283, 316, 387, 501, 560
– of interface control 17, 165, 239, 431
– of nucleation 13, 49, 115
– of relaxation 32

Lasers, crystals for
– frequency conversion 199
Lead
– chloride 115, 612
– di-iodide 453
– selenide 271
– sulphate 115
– tin selenide 271
Lithium
– niobate 145

Magnesium
– telluride 607
Melt growth technique
– by Bridgman–Stockbarger method
– – of cesium iodide 230
– – of gallium germanium 165
– – of germanium 75
– – of gold silver telluride 518
– – of lead chloride 612
– – of silver gallium sulphide 41
– – of ternary alkali lead chlorides 612
– by Czochralski method
– – of barium metaborate 199
– – of gadolinium molybdate 598
– – of lithium niobate 145
– – of neodymium gallium oxide 413
– – of rare earth orthoaluminates 616
– – of silicon 247
– – of terbium molybdate 598
– – theory of 247, 481, 598
– by floating zone method
– – of gallium arsenide 17, 83
– – theory of 209, 481
– by Kyropoulos method
– – of gold silver telluride 518
– by miniature pedestal method
– – of alumina 457
– – of gallium scandium aluminum garnet 457
– by uniaxial solidification
– – of ice 153
– by zone melting
– – theory of 209
– theory of 431
Mercury
– cadmium telluride 124, 565
– zinc telluride 574
Microgravity, growth under
– of gallium germanium 165
Morphological stability
– of ammonium chloride dendrites 111
– of calcite 533
– of calcium hydrogen orthophosphate dihydrate 331
– of gallium arsenide 17
– of gallium indium arsenide phosphide 309
– of growth face of gallium arsenide 17
– theory of 209

Neodymium
– gallium oxide 138, 413
Nucleation
– of lead chloride 115
– of lead sulphate 115
– of silicon carbide 71
Numbers
– Grashof 145
– Marangoni 145
– Rayleigh 145

n-Paraffin 13
Phase diagrams
– of barium metaborate/sodium oxide/sodium fluoride 109
– of cesium iodide/tellurium iodide 230
– of potassium fluoride/yttrium aluminum garnet 181
– of potassium lithium tantalate niobate 486
– of silver gallium sulphide 41
– of zinc selenide 277
Polymers 501
Potassium
– bromide 395
– lithium tantalate niobate 486
– neodymium silicates 352
Precursor
– for gallium arsenide 176
– for zinc selenide 49
Purification of materials
– of lead chloride 612

Quantum wells, see Device characterization
Quartz 560
Rare earth
– orthoaluminates 616
Residual gas in silica glas ampoule 193

Silicon 247, 265, 316, 495, 589
– carbide 5, 71
– di-oxide 560
– germanium 32
Silver
– gallium sulphide 41
Sodium
– neodymium silicates 373
– tungsten bronzes 473
– yttrium silicates 373
Solid growth technique
– by recrystallization
– – of mercury cadmium telluride 565
– – of potassium bromide 395
– by strain anneal
– – of mercury cadmium telluride 565
– theory of 395
Solution growth technique
– by electrocrystallization
– – of lead chloride 115
– – of lead sulphate 115

– by flux method
– – of barium hexaferrite 97
– – of bismuth strontium calcium cuprate 105
– – of cesium titanyl arsenate 323
– – of iron sulphide 448
– – of yttrium aluminum garnet 181
– by flux method, top seeded
– – of barium metaborate 199
– of hydrothermal growth
– – of potassium neodymium silicates 352
– – of quartz 560
– – of sodium neodymium silicates 373
– – of sodium yttrium silicates 373
– by room temperature method
– – of calcium hydrogen orthophosphate dihydrate 331
– by top seeded growth
– – of potassium lithium tantalate niobate 486
– theory of 560
Stefan problem or moving boundary problem
– theory of 209
Superconductivity materials, high T_c
– bulk
– – of BiSCCO 105
Superlattices, multilayers
– of III–V compounds 1
Surface energy, determination
– of calcite 533
– of gallium antimonide 157
– of indium antimonide 157
– of polymers 501
Surface structure
– of calcite 533
– of cerium dioxide 347
– of zinc selenide 277

Terbium
– molybdate 598
Ternary alkali lead chlorides 612
Thin film growth, epitaxy
– by atomic layer epitaxy
– – of gallium arsenide 61
– by chemical beam epitaxy
– – of gallium indium arsenide 387
– – of gallium indium phosphide 387
– – of gallium indium phosphide 387
– – theory of 387
– by chemical reaction
– – of silicon carbide 5
– by gas source molecular beam epitaxy
– – of gallium arsenide phosphide 309
– by liquid phase electroepitaxy
– – of aluminum gallium arsenide 426
– by liquid phase epitaxy
– – of aluminum gallium arsenide 426
– – of gallium arsenide 17
– of metalorganic molecular beam epitaxy
– – of gallium indium arsenide 387
– – of gallium indium arsenide phosphide 387
– – of gallium indium phosphide 387
– – of zinc selenide 49
– – theory of 387
– by molecular beam epitaxy
– – of aluminum gallium indium arsenide 419
– – of aluminum indium arsenide 419
– – of cadmium telluride 607
– – of gallium antimonide 620
– – of gallium arsenide/gallium indium arsenide 1
– – of gallium phosphide 465
– – of indium arsenide 300, 465, 620
– – of indium phosphide 465
– – of magnesium telluride 607
– – of silicon 316
– – of zinc selenide 277
– by radio frequency sputtering
– – of neodymium gallium oxide 138
– – of zinc oxide 546
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of silicon 495, 589
– – – of silicon germanium 32
– – – theory of 589
– – through evaporation and condensation
– – – of cerium dioxide 347
– – – of n-paraffin 13
– – – of silicon carbide 71
– – through metalorganic chemical vapor deposition
– – – of cadmium telluride 133
– – – of copper aluminum selenide 551
– – – of gallium arsenide 176, 283
– – – of indium aluminum arsenide 186
– – – of indium phosphide 204
– – – of mercury cadmium telluride 124
– – – of zinc selenide 49
– – – theory of 283
Tin
– disulphide 268
Tungsten 439

Vapor growth technique
– by chemical transport
– – of mercury zinc telluride 574
– – theory of 574
– by evaporation and condensation
– – of lead di-iodide 453
– – of tin disulphide 268
– – of tungsten 439

Whisker growth
– of sodium tungsten bronzes 473

Yttrium
– aluminum garnet 181

Zinc
– oxide 546
– selenide 49, 277